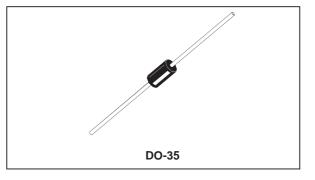


BAT41

SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching. This device has integrated protection against excessive voltage such as electrostatic discharges.



ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | Value | Unit | |
|------------------------|--|---|------------------------------|---------|
| V _{RRM} | Repetitive Peak Reverse Voltage | 100 | V | |
| ١ _F | Forward Continuous Current* | 100 | mA | |
| I _{FRM} | Repetitive Peak Forward Current* | $ \begin{array}{l} \mbox{tritive Peak Forward Current}^{*} & t_{p} \leq \mbox{1s} \\ \delta \leq \mbox{0.5} \end{array} $ | | mA |
| I _{FSM} | Surge non Repetitive Forward Current* $t_p \le 10ms$ | | 750 | mA |
| P _{tot} | Power Dissipation* T _a = 95°C | | 100 | mW |
| T _{stg} Tj | Storage and Junction Temperature Range | | - 65 to +150 - 65 to +125 | °C ℃ |
| TL | Maximum Lead Temperature for Soldering du from Case | 230 | °C | |

THERMAL RESISTANCE

| Symb | Test Conditions | Value | Unit |
|---------------------|-------------------|-------|------|
| R _{th(j-a} | Junction-ambient* | 300 | °C/W |

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

| Symbol | Test Conditions | | | Min. | Тур. | Max. | Unit |
|--------------------|------------------------|------------------------|----------------------|------|------|------|------|
| V _{BR} | T _j = 25°C | I _R = 100μA | | 100 | | | V |
| V _F * * | T _j = 25°C | $I_F = 1 m A$ | | | 0.4 | 0.45 | V |
| | T _j = 25°C | I _F = 200mA | | | | 1 | |
| I _R * * | T _j = 25°C | | V _R = 50V | | | 0.1 | μA |
| | T _j = 100°C | | | | | 20 | |

DYNAMIC CHARACTERISTICS

| Symbol | Test Conditions | | | Min. | Тур. | Max. | Unit |
|--------|---------------------|------------|----------|------|------|------|------|
| С | $T_j = 25^{\circ}C$ | $V_R = 1V$ | f = 1MHz | | 2 | | pF |

* On infinite heatsink with 4mm lead length * * Pulse test: $t_p\!\leq\!300\mu s~\delta\!<\!2\%$.

10~2

0

25



10³

10²

10

1

10⁻¹

10⁻²

10²

0

I_Π (μΑ)

I_f (mA)

Fig. 1: Forward current versus forward voltage at different temperatures (typical values).

⊊Ťi

¯τ_j =

= <u>∑</u> T_j =

1

T_i

100

125

75

125°C

25°C

55°C

(V) ٧_F

1.2 1.4

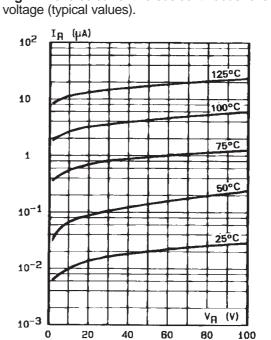
Fig. 3: Reverse current versus junction temperature.

0.2 0.4 0.6 0.8

90 % confidence V_R = 50 V 10 max typ. 1 10⁻¹ (°C)

50

Fig. 4: Reverse current versus continuous reverse



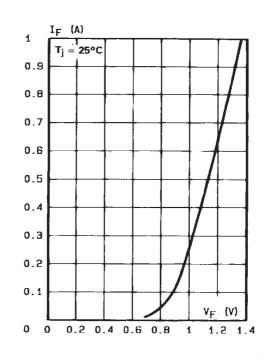


Fig. 2: Forward current versus forward voltage (typical values).

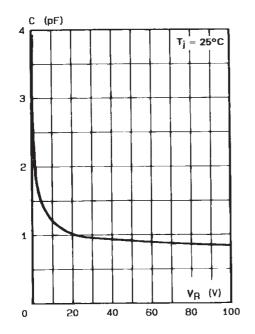
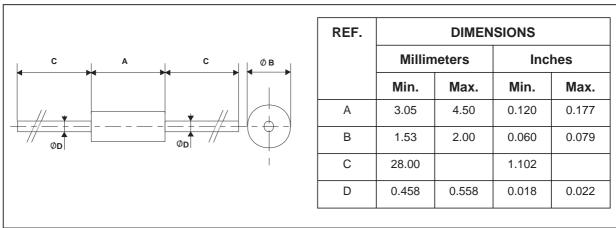


Fig. 5: Capacitance C versus reverse applied voltage $V_{_{\rm R}}$ (typical values).

PACKAGE MECHANICAL DATA

DO-35



Cooling method : by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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